MK41H78/79(N,P) -20/25/35

4K x 4 CMOS STATIC RAM

- 20, 25, AND 35ns ADDRESS ACCESS TIME
- EQUAL ACCESS AND CYCLE TIMES
- 22-PiN, 300 MIL PLASTIC
- ALL INPUTS AND OUTPUTS TTL COMPATI-BLE, LOW CAPACITANCE, AND PROTECTED AGAINST STATIC DISCHARGE
- TTL STANDBY CURRENT UNAFFECTED BY ADDRESS ACTIVITY
- SEPARATE OUTPUT ENABLE CONTROL
- FLASH CLEAR FUNCTION

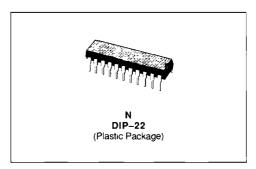
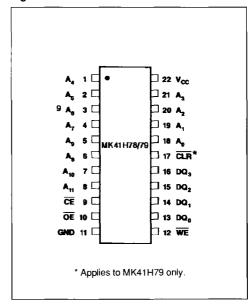


Figure 1: Pin Connection.



DESCRIPTION

The MK41H78/79 features fully static operation requiring no external clocks or timing strobes, and equal address access and cycle times. It requires a single + $5V \pm 10$ percent power supply and is fully TTL compatible.

The device has a Chip Enable power down feature which automatically reduces power dissipation when the $\overline{\text{CE}}$ pin is brought inactive (high). Standby power can be further reduced by raising the $\overline{\text{CE}}$ pin to the full V_{CC} voltage. An Output Enable ($\overline{\text{OE}}$) pin provides a high speed tristate control, allowing fast read/write cycles to be achieved with the common-I/O data bus.

Flash Clear operation is provided on the MK41H79 via the CLR pin, and CE active (low). A low applied to the CLR pin clears all RAM bits to zero, making it especially useful for high speed cache and buffer storage applications.

PIN NAMES

A ₀ - A ₁₁ - Address	OE - Ouput Enable
DQ ₀ - DQ ₃ - Data I/O	WE - Write Enable
CLR - Flash Clear	GND - Ground
CE - Chip Enable	V _{CC} - + 5V

ABSOLUTE MAXIMUM RATINGS*

Parameter	Value	Unit
Voltage on any Pin Relative to GND	- 1.0 to + 7.0	V
Ambient Operating Temperture (T _A)	0 to 70	°C
Ambient Storage Temperature (plastic)	- 55 to + 125	Ĉ.
Ambient Storage Temperature (ceramic)	- 65 to +150	,C
Total Device Power Dissipation	1	w
Output Currrent per Pin	50	mA

Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or other conditions beyond those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

TRUTH TABLE

CE	ŌĒ	WE	CLR *	Mode	DQ	Power
Н	Х	Х	Х	Deselect	High Z	Standby
L	X	L	Н	Write	D _{IN}	Active
L	L	Н	Н	Read	D _{OUT}	Active
Ļ	Н	н	H	Read	High Z	Active
L	Х	L	L	Flash Clear	High Z	Active
L	L	Н	L	Flash Clear	Low Z	Active
L	Н	Н	L	Flash Clear	High Z	Active

X = Don't Care

RECOMMENDED DC OPERATING CONDITIONS (0°C \leq T_A \leq 70°C)

Symbol	Parameter		Value					
Symbol	Farameter	Min.	Тур.	Max.]	Notes		
Vcc	Supply Voltage	4.5	5.0	5.5	V	3		
GND	Supply Voltage	0	0	0	V			
V _{IH}	Logic 1 Voltage, All Inputs	2.2		V _{CC} + 1.0	٧	3		
V _{IL}	Logic 0 Voltage, All Inputs	- 0.3		0.8	V	3		

DC ELECTRICAL CHARACTERISTICS (0°C \leq T_A \leq 70°C) (V_{CC} = 5.0V \pm 10 percent)

١	Symbol	Parameter		Unit	Notes		
	Symbol	Parameter	Min.	Тур.	Max.	0	Hotes
	I _{CC1}	Average Power Supply Current			120	mA	4
	I _{CC2}	TTL Standby Current			16	mA	5
ĺ	I _{CC3}	CMOS Standby Current			8	mA	6
ĺ	I _{IL}	Input Leakage Current (any input pin)	- 1		+ 1	μΑ	7
Ī	loL	Output Leakage Current (any output pin)	- 10		+ 10	μА	8
ĺ	V _{OH}	Output Logic 1 Voltage (I _{OUT} = - 4 mA)	2.4			V	3
ĺ	Vol	Output Logic 0 Voltage (I _{OUT} = + 8 mA)			0.4	V	3

^{*} Applies to MK41H79 only.

CAPACITANCE ($T_A = 25^{\circ}C$, f = 1.0MHz)

Symbol	Symbol Parameter		Value		Hnit	Notes
	T dramotor	Min.	Typ.	Max.	• • • • • • • • • • • • • • • • • • •	Notes
C ₁	Capacitance on Input Pins	4		5	pF	9
C ₂	Capacitance on DQ Pins	8		10	pF	9

- Notes: 1. Measured with load shown in figure 2(A).
 - 2. Measured with load shown in figure 2(B).
 - 3. All voltages referenced to GND.
 - 4. lcc1 is measured as the average AC current with Vcc = Vcc (max) and with the outputs open circuit tac = tac (min) is used.

 - 5. CE = V_{IH}, all <u>other</u> inputs = Don't Care. 6. Vcc (max) ≥ CE ≥ Vcc 0.3V, all other inputs = Don't Care.

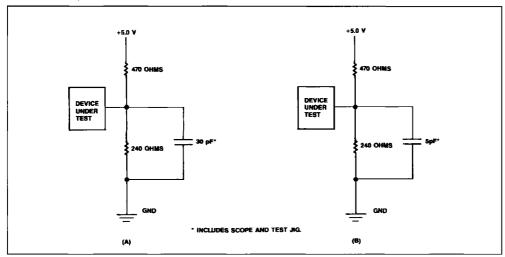
 - 8. Output leakage current specifications are valid for all V_{IN} such that 0V < V_{IN} < V_{CC}. Measured at V_{CC} = V_{CC} (max).

 8. Output leakage current specifications are valid for all V_{OUT} such that 0V < V_{OUT} < V_{CC}, CE = V_{IH} and V_{CC} in valid

AC TEST CONDITIONS

Ambient Temperature0°C to 70°C

Figure 2: Output Load Circuits.



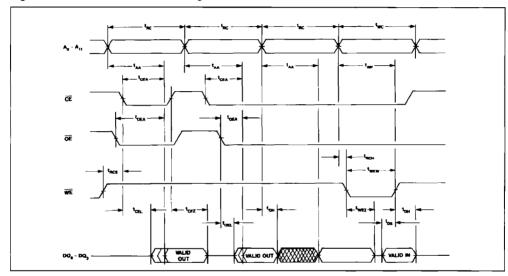
OPERATIONS

READ MODE

The MK41H78/79 is in the Read Mode whenever WE (Write Enable) is high and CE (Chip Enable) is low, providing a ripple-through access to data from four of 16,384 locations in the static storage array. The unique address specified by the 12 Address Inputs defines which one of 4096 nibbles of data is to be accessed.

Figure 3: Read-read-write Timing.

Valid data will be available at the four Data Output pins within taa after the last address input signal is stable, providing that the CE and $\overline{\text{OE}}$ (output Enable) access times are satisfied. If CE or OE access times are not met, data access will be measured from the limiting parameter (tcea or toea) rather than the address. The state of the four Data I/O pins is controlled by the CE, WE and OE control signals. The data lines may be in an indeterminate state at tcel and toel, but the data lines will always have valid data at taa.



AC ELECTRICAL CHARACTERISTICS (read cycle timing) $(0^{\circ}C \le T_{A} \le 70^{\circ}C)$ ($V_{CC} = 5.0V \pm 10$ percent)

		MK411	17X-20	MK411	H7X-25	MK41H7X-35			l., .
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Notes
t _{RC}	Read Cycle Time	20		25		35		пѕ	
t _{AA}	Address Access Time		20		25		35	ns	1
t _{CEL}	Chip Enable to Low-Z	7		7		7		ns	2
t _{CEA}	Chip Enable Access Time		20		25		35	ns	1
t _{OEL}	Output Enable to Low-Z	2		2		2		ns	2
t _{OEA}	Output Enable Access Time		10		12		15	ns	1
tacs	Read Command Setup Time	0		0		0		ns	
t _{RCH}	Read Command Hold Time	0		0		0		ns	
t _{OH}	Valid Data Out Hold Time	5		5		5		ns	1
t _{CEZ}	Chip Enable to High-Z		8		10		13	ns	2
t _{OEZ}	Output Enable to High-Z		7		8		10	ns	2
t _{wez}	Write Enable to High-Z		8		10		13	ns	2

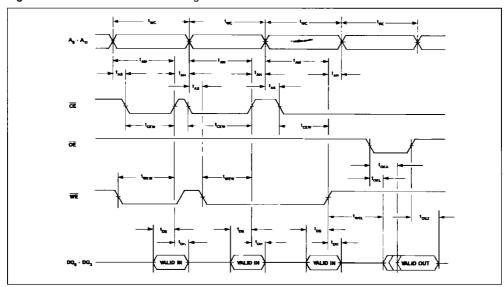
WRITE MODE

The MK41H78/79 is in the Write Mode whenever the WE and CE inputs are in the low state. CE or WE must be high during address transitions. Addresses must be held valid throughout a write cycle. The Write begins with the concurrence of a low on WE and CE. Therefore, tas is referenced to the latter oc-

curring edge of $\overline{\text{CE}}$ or WE. The write cycle is terminated by the earlier rising edge of $\overline{\text{CE}}$ or WE.

If the output is enabled $(\overline{CE} \text{ and } \overline{OE} \text{ low})$, then \overline{WE} will return the outputs to high impedance within twez of its falling edge. Care must be taken to avoid bus contention in this type of operation. Data-In must remain valid toH after the rising edge of \overline{CE} or \overline{WE} .

Figure 4: Write-write-read Timing



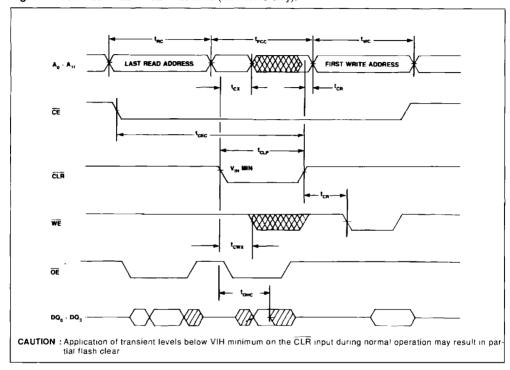
AC ELECTRICAL CHARACTERISTICS (write cycle timing) (0°C \leq T_A \leq 70°C) (V_{CC} = 5.0V \pm 10 percent)

		MK41I	MK41H7X-20		MK41H7X-25		MK41H7X-35		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Notes
twc	Write Cycle Time	20		25		35		ns	
t _{AS}	Address Setup Time	0		0		0		ns	
t _{AW}	Address Stable to End of Write	16		20		30		ns	
t _{AH}	Address Hold after End of Write	0		0		0		ns	
t _{CEW}	Chip Enable to End of Write	18		22		32		ns	
t _{WEW}	Write Enable to End of Write	16		20		30		ns	
t _{DS}	Data Setup Time	12		14		15		ns	
t _{DH}	Data Hold Time	0		0		0		ns	
t _{WEL}	Write Enable to Low-Z	5		5		5		ns	2

FLASH CLEAR

A Flash Clear cycle sets all 16,384 bits in the RAM to logic zero. A Clear begins at the concurrence of a low on Chip Enable (CE) and Flash Clear (CLR). A Clear may be ended by a high on either CE or CLR. A low on CLR has no effect if the device is disabled (CE high). A Clear may be executed within either a Read or a Write cycle. Figure 4 illustrates a Clear within a Read cycle. Clears within Write cycles are constrained only in that Write timing parameters must be observed as soon as the Flash Clear pin returns high.

Figure 5: Last Read-flash Clear-first Write (MK41H79 only).



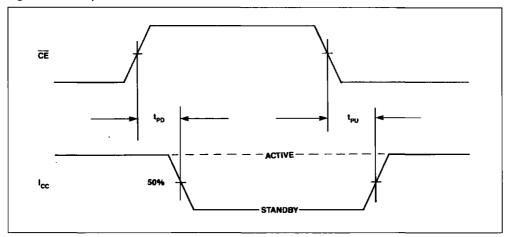
AC ELECTRICAL CHARACTERISTICS (clear cycle timing) (0°C \leq T_A \leq 70°C) (V_{CC} = 5.0 \pm 10%)

		MK411	MK41H7X-20		MK41H7X-25		MK41H7X-35		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Notes
t _{FCC}	Flash Clear Cycle Time	40		50		70		ns	
t _{CEC}	Chip Enable Low to End of Clear	40		50		70		ns	
T _{CLP}	Flash Clear Low to End of Clear	38		48		68		ns	
t _{cx}	Clear to Inputs Don't Care	0		0		0		ns	
ţ _{CR}	End of Clear to Inputs Recognized	0		0		0		ns	
tcwx	Clear to Write Enable Don't Care	0		0		0		ns	
t _{OHC}	Valid Data Out Hold from Clear	5		5		5		ns	1

STANDBY MODE

The MK41H78/79 is in Standby Mode whenever \overline{CE} is held at or above V_{IH} .

Figure 6: Standby Mode.



AC ELECTRICAL CHARACTERISTICS (standby mode) $(0^{\circ}C \le T_A \le 70^{\circ}C)$ ($V_{CC} = 5.0V \pm 10$ percent)

0 111			MK41H7X-20 MK		MK41H7X-25		MK41H7X-35		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Notes
t _{PD}	Chip Enable High to Power Down		20		25		35	ns	
t _{⊬U}	Chip Enable Low to Power up	0		0		0		ns	

APPLICATION

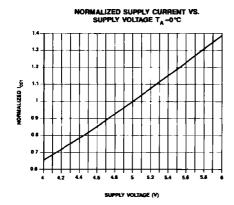
The MK41H78/79 operates from a 5.0 volt supply. It is compatible with all standard TTL families on all inputs and outputs. The device should share a solid ground plane with any other devices interfaced with it, particularly TTL devices. Additionally, because the outputs can drive rail-to-rail into high impedance loads, the 41H79 can also interface to 5 volt CMOS on all inputs and outputs. Refer to the normalized performance curves that follow.

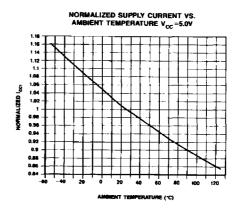
Since very high frequency current transients will be associated with the operation of the MK41H79, power line inductance must be minimized on the circuit board power distribution network. Power and ground tracegridding or separate power planes can be employed to reduce line inductance. Additionally, a high frequency decoupling capacitor should be

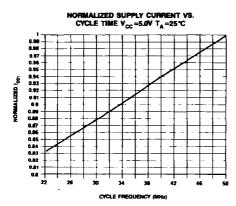
placed next to each RAM. The capacitor should be $0.1\mu F$ or larger. A pull-up resistor is also recommended for CLR on the MK41H79. This will ensure that any low going system noise, coupled onto the input, does not drive CLR below V_{IH} minimum specifications.

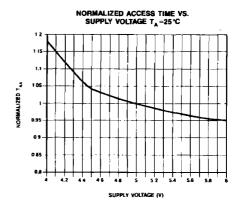
Though often times not thought of as such, the traces on a memory board are basically unterminated, low impedance transmission lines. As such they are subject to signal reflections manifested as noise, undershoots and excessive ringing. Series termination in close proximity to the TTL drivers can improve driver/signal path impedance matching. While experimentation most often proves to be the only practical approach to selection of series resistors, values in the range of 10 to 33 Ω often prove most suitable.

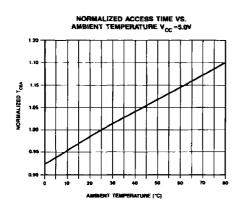
NORMALIZED DC AND AC PERFORMANCE CHARACTERISTICS

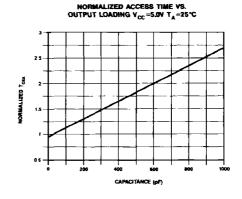




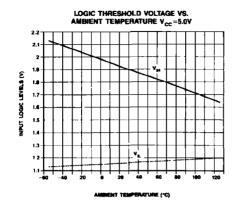


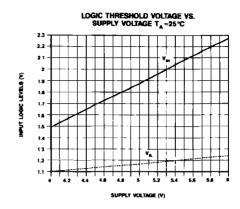


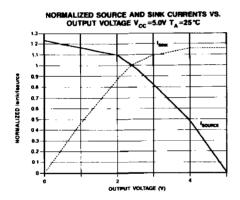


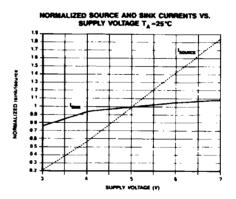


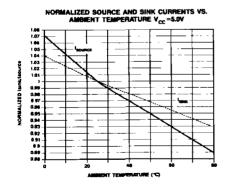
NORMALIZED DC AND AC PERFORMANCE CHARACTERISTICS

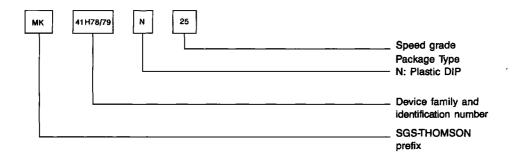








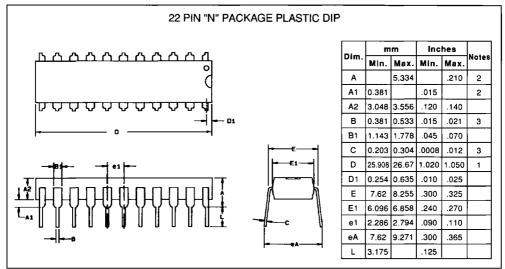




ORDER CODES

Part Number	Access Time	Package Type	Temperature Range
MK41H78N-20	20ns	22 Pin Plastic DIP	0°C to 70°C
MK41H78N-25	25ns	22 Pin Plastic DIP	0°C to 70°C
MK41H78N-35	35ns	22 Pin Plastic DIP	0°C to 70°C
MK41H79N-20	20ns	22 Pin Plastic DIP	0°C to 70°C
MK41H79N-25	25ns	22 Pin Plastic DIP	0°C to 70°C
MK41H79N-35	35ns	22 Pin Plastic DIP	0°C to 70°C

PACKAGE DESCRIPTION



Notes: 1. Overall length includes 010 in flash on either end of the package

2. Package standoff to be measured per jedec requirements.

3. The maximum limit shall be increased by 003 in when solder lead finish is specified.